

# Complementary Bias Resistor Transistors

**R1 = 4.7 kΩ, R2 = ∞ kΩ**

NPN and PNP Transistors with Monolithic Bias Resistor Network

## MUN5316DW1, NSBC143TPDXV6

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias resistor network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

### Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable\*
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

(T<sub>A</sub> = 25°C both polarities Q1 (PNP) and Q2 (NPN), unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	30	Vdc
Input Reverse Voltage -NPN -PNP	V <sub>IN(rev)</sub>	6 5	Vdc

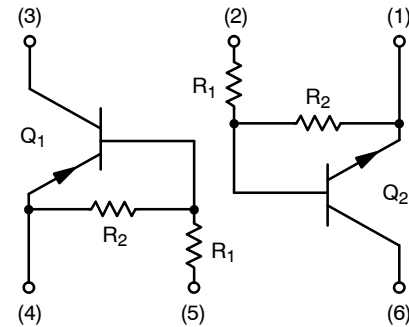
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### ORDERING INFORMATION

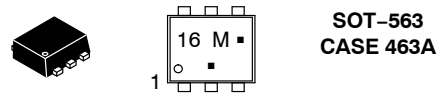
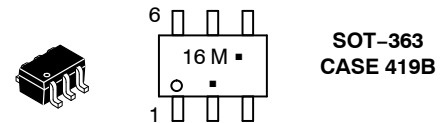
Device	Package	Shipping†
MUN5316DW1T1G NSVMUN5316DW1T1G*	SOT-363	3,000 / Tape & Reel
NSBC143TPDXV6T1G, NSVBC143TPDXV6T1G*	SOT-563	4,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### PIN CONNECTIONS



### MARKING DIAGRAMS



- 16 = Specific Device Code
- M = Date Code\*
- = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

# MUN5316DW1, NSBC143TPDXV6

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
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### MUN5316DW1 (SOT-363) One Junction Heated

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1)	$P_D$	187	mW
Derate above $25^\circ\text{C}$ (Note 2)		256	
(Note 1)		1.5	mW/ $^\circ\text{C}$
(Note 2)		2.0	
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	670	$^\circ\text{C}/\text{W}$
(Note 2)		490	

### MUN5316DW1 (SOT-363) Both Junction Heated (Note 3)

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1)	$P_D$	250	mW
Derate above $25^\circ\text{C}$ (Note 2)		385	
(Note 1)		2.0	mW/ $^\circ\text{C}$
(Note 2)		3.0	
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	493	$^\circ\text{C}/\text{W}$
(Note 2)		325	
Thermal Resistance, Junction to Lead (Note 1)	$R_{\theta JL}$	188	$^\circ\text{C}/\text{W}$
(Note 2)		208	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

### NSBC143TPDXV6 (SOT-563) One Junction Heated

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1)	$P_D$	357	mW
Derate above $25^\circ\text{C}$ (Note 1)		2.9	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$

### NSBC143TPDXV6 (SOT-563) Both Junction Heated (Note 3)

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1)	$P_D$	500	mW
Derate above $25^\circ\text{C}$ (Note 1)		4.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. Both junction heated values assume total power is sum of two equally powered channels.

# MUN5316DW1, NSBC143TPDXV6

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ both polarities $Q_1$ (PNP) and $Q_2$ (NPN), unless otherwise noted)

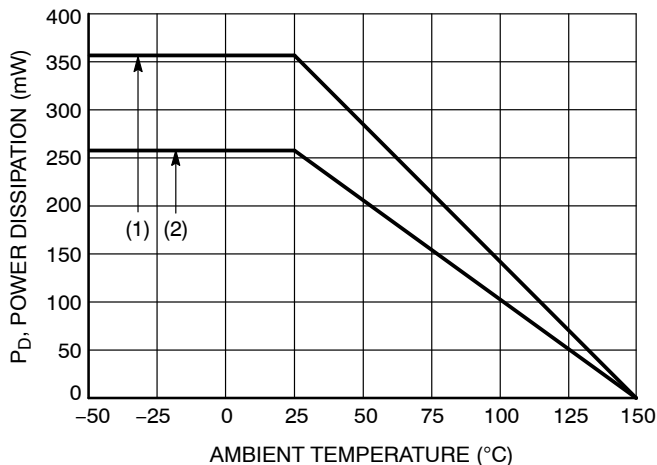
Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Base Cutoff Current ( $V_{CB} = 50\text{ V}$ , $I_E = 0$ )	$I_{CBO}$	-	-	100	nAdc
Collector-Emitter Cutoff Current ( $V_{CE} = 50\text{ V}$ , $I_B = 0$ )	$I_{CEO}$	-	-	500	nAdc
Emitter-Base Cutoff Current ( $V_{EB} = 6.0\text{ V}$ , $I_C = 0$ )	$I_{EBO}$	-	-	1.9	mAdc
Collector-Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 4) ( $I_C = 2.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	50	-	-	Vdc

## ON CHARACTERISTICS

DC Current Gain (Note 4) ( $I_C = 5.0\text{ mA}$ , $V_{CE} = 10\text{ V}$ )	$h_{FE}$	160	350	-	
Collector-Emitter Saturation Voltage (Note 4) ( $I_C = 10\text{ mA}$ , $I_B = 0.3\text{ mA}$ )	$V_{CE(sat)}$	-	-	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0\text{ V}$ , $I_C = 100\ \mu\text{A}$ ) (NPN) ( $V_{CE} = 5.0\text{ V}$ , $I_C = 100\ \mu\text{A}$ ) (PNP)	$V_{i(off)}$	-	0.6 0.58	-	Vdc
Input Voltage (on) ( $V_{CE} = 0.2\text{ V}$ , $I_C = 10\text{ mA}$ ) (NPN) ( $V_{CE} = 0.2\text{ V}$ , $I_C = 10\text{ mA}$ ) (PNP)	$V_{i(on)}$	-	0.9 1.0	-	Vdc
Output Voltage (on) ( $V_{CC} = 5.0\text{ V}$ , $V_B = 2.5\text{ V}$ , $R_L = 1.0\text{ k}\Omega$ )	$V_{OL}$	-	-	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0\text{ V}$ , $V_B = 0.5\text{ V}$ , $R_L = 1.0\text{ k}\Omega$ )	$V_{OH}$	4.9	-	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	k $\Omega$
Resistor Ratio	$R_1/R_2$	-	-	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq$  2%.



- (1) SOT-363; 1.0 x 1.0 inch Pad
- (2) SOT-563; Minimum Pad

Figure 1. Derating Curve

# MUN5316DW1, NSBC143TPDXV6

## TYPICAL CHARACTERISTICS - NPN TRANSISTORS MUN5316DW1, NSBC143TPDXV6

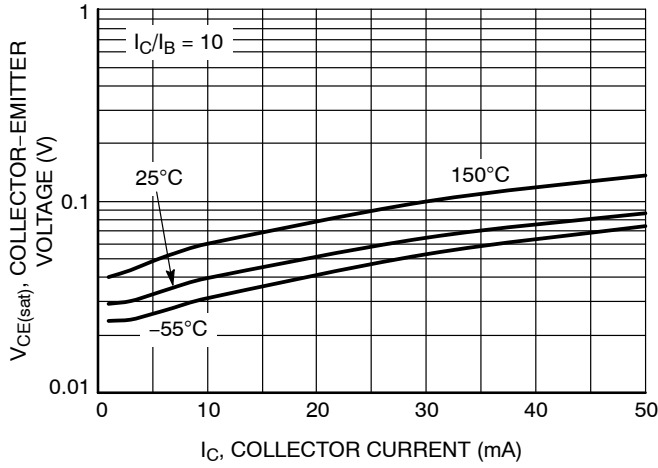


Figure 2.  $V_{CE(sat)}$  vs.  $I_C$

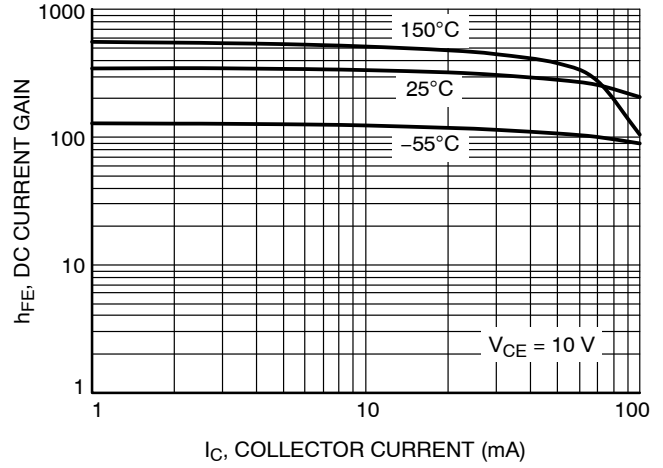


Figure 3. DC Current Gain

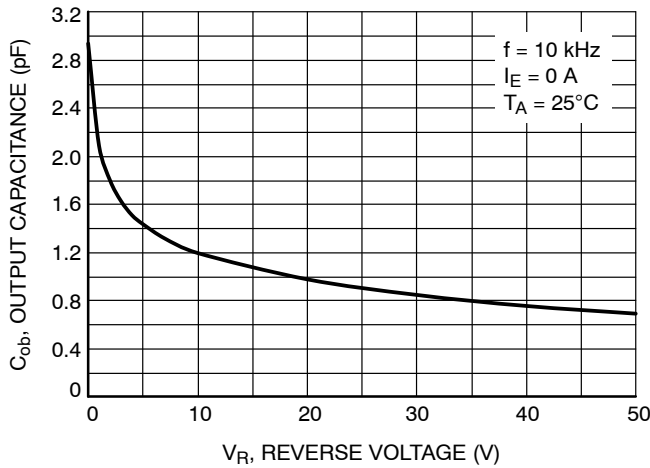


Figure 4. Output Capacitance

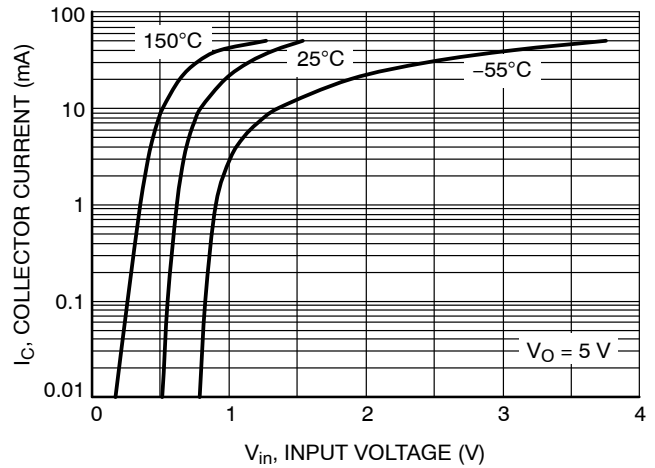


Figure 5. Output Current vs. Input Voltage

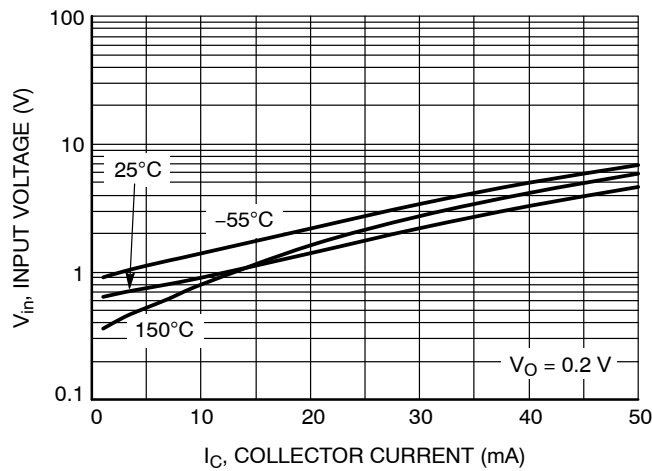


Figure 6. Input Voltage vs. Output Current

# MUN5316DW1, NSBC143TPDXV6

## TYPICAL CHARACTERISTICS – PNP TRANSISTORS MUN5316DW1, NSBC143TPDXV6

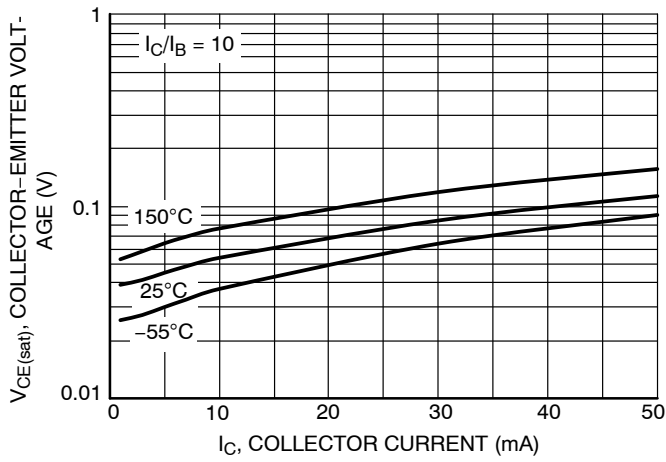


Figure 7.  $V_{CE(sat)}$  vs.  $I_C$

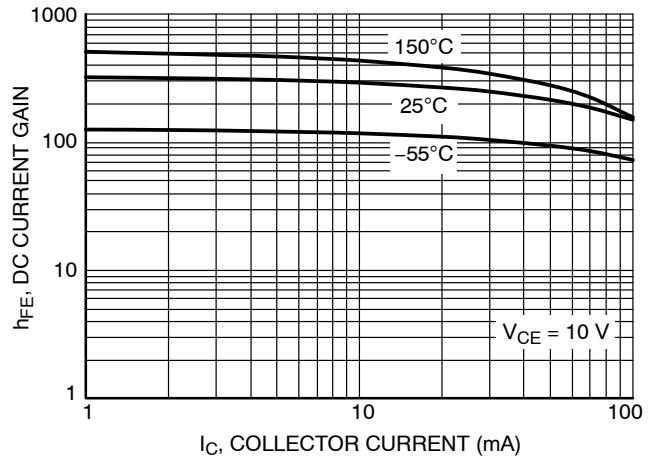


Figure 8. DC Current Gain

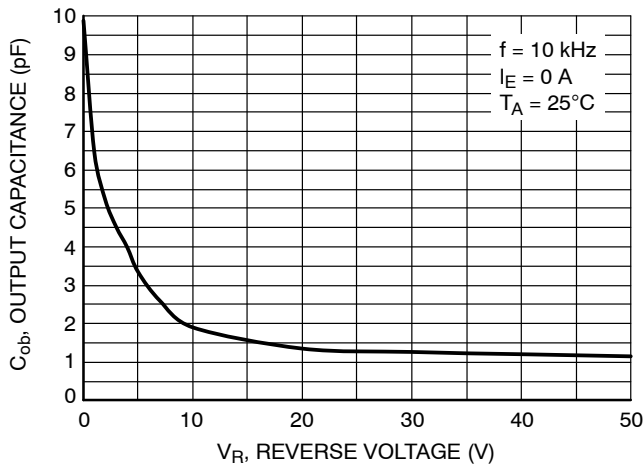


Figure 9. Output Capacitance

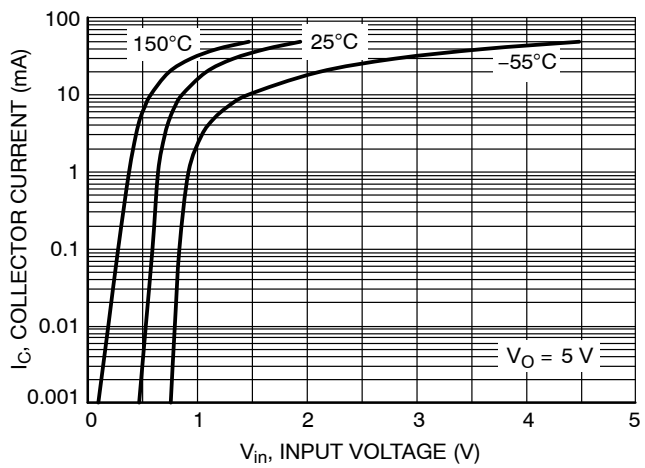


Figure 10. Output Current vs. Input Voltage

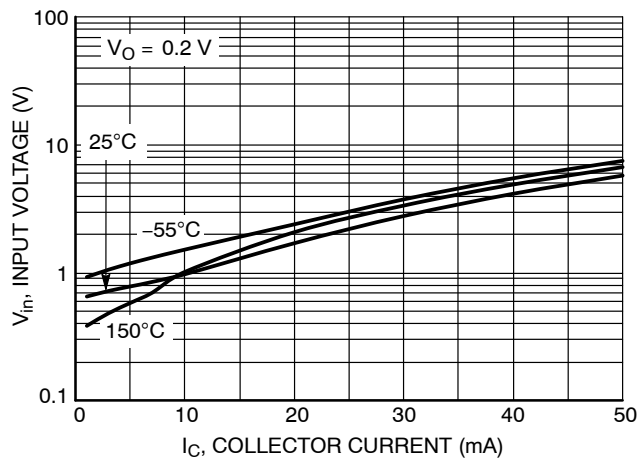


Figure 11. Input Voltage vs. Output Current

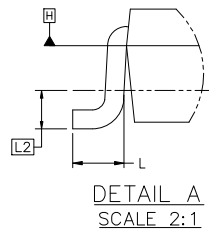
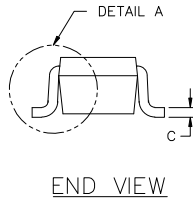
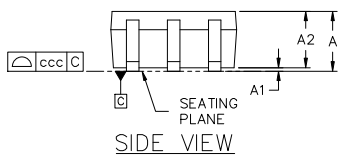
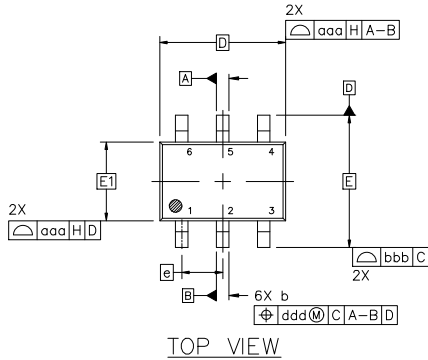


SC-88 2.00x1.25x0.90, 0.65P  
CASE 419B-02  
ISSUE Z

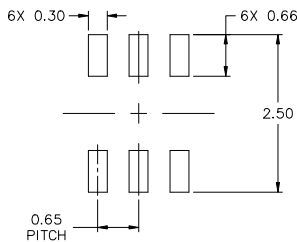
DATE 18 APR 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

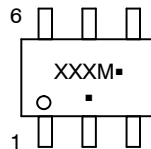


DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DESCRIPTION:	SC-88 2.00x1.25x0.90, 0.65P	PAGE 1 OF 2

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**SC-88 2.00x1.25x0.90, 0.65P**  
**CASE 419B-02**  
**ISSUE Z**

DATE 18 APR 2024

<b>STYLE 1:</b> PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	<b>STYLE 2:</b> CANCELLED	<b>STYLE 3:</b> CANCELLED	<b>STYLE 4:</b> PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	<b>STYLE 5:</b> PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	<b>STYLE 6:</b> PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
<b>STYLE 7:</b> PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	<b>STYLE 8:</b> CANCELLED	<b>STYLE 9:</b> PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	<b>STYLE 10:</b> PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	<b>STYLE 11:</b> PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	<b>STYLE 12:</b> PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
<b>STYLE 13:</b> PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	<b>STYLE 14:</b> PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	<b>STYLE 15:</b> PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	<b>STYLE 16:</b> PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	<b>STYLE 17:</b> PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	<b>STYLE 18:</b> PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
<b>STYLE 19:</b> PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	<b>STYLE 20:</b> PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	<b>STYLE 21:</b> PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	<b>STYLE 22:</b> PIN 1. D1 (i) 2. GND 3. D2 (j) 4. D2 (c) 5. VBUS 6. D1 (c)	<b>STYLE 23:</b> PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	<b>STYLE 24:</b> PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
<b>STYLE 25:</b> PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	<b>STYLE 26:</b> PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	<b>STYLE 27:</b> PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	<b>STYLE 28:</b> PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	<b>STYLE 29:</b> PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	<b>STYLE 30:</b> PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

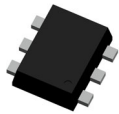
Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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<b>DESCRIPTION:</b>	<b>SC-88 2.00x1.25x0.90, 0.65P</b>	<b>PAGE 2 OF 2</b>

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

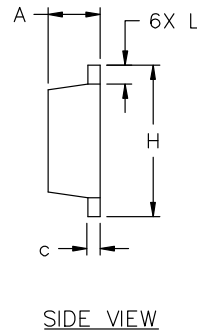
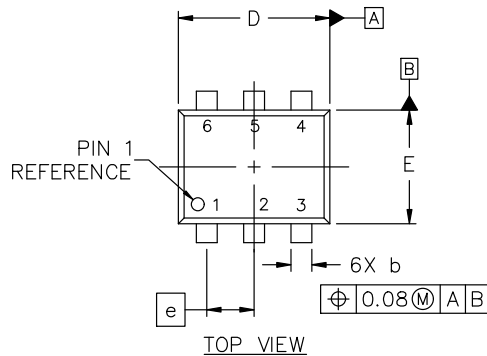


**SOT-563-6 1.60x1.20x0.55, 0.50P**  
**CASE 463A**  
**ISSUE J**

DATE 15 FEB 2024

**NOTES:**

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30

**STYLE 1:**  
 PIN 1. EMITTER 1  
 2. BASE 1  
 3. COLLECTOR 2  
 4. EMITTER 2  
 5. BASE 2  
 6. COLLECTOR 1

**STYLE 2:**  
 PIN 1. EMITTER 1  
 2. EMITTER 2  
 3. BASE 2  
 4. COLLECTOR 2  
 5. BASE 1  
 6. COLLECTOR 1

**STYLE 3:**  
 PIN 1. CATHODE 1  
 2. CATHODE 1  
 3. ANODE/ANODE 2  
 4. CATHODE 2  
 5. CATHODE 2  
 6. ANODE/ANODE 1

**STYLE 4:**  
 PIN 1. COLLECTOR  
 2. COLLECTOR  
 3. BASE  
 4. EMITTER  
 5. COLLECTOR  
 6. COLLECTOR

**STYLE 5:**  
 PIN 1. CATHODE  
 2. CATHODE  
 3. ANODE  
 4. ANODE  
 5. CATHODE  
 6. CATHODE

**STYLE 6:**  
 PIN 1. CATHODE  
 2. ANODE  
 3. CATHODE  
 4. CATHODE  
 5. CATHODE  
 6. CATHODE

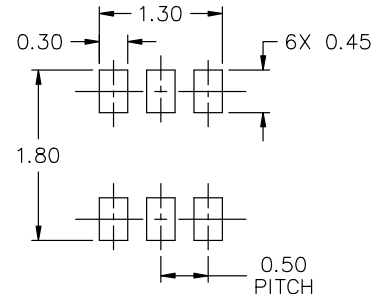
**STYLE 7:**  
 PIN 1. CATHODE  
 2. ANODE  
 3. CATHODE  
 4. CATHODE  
 5. ANODE  
 6. CATHODE

**STYLE 8:**  
 PIN 1. DRAIN  
 2. DRAIN  
 3. GATE  
 4. SOURCE  
 5. DRAIN  
 6. DRAIN

**STYLE 9:**  
 PIN 1. SOURCE 1  
 2. GATE 1  
 3. DRAIN 2  
 4. SOURCE 2  
 5. GATE 2  
 6. DRAIN 1

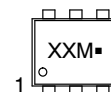
**STYLE 10:**  
 PIN 1. CATHODE 1  
 2. N/C  
 3. CATHODE 2  
 4. ANODE 2  
 5. N/C  
 6. ANODE 1

**STYLE 11:**  
 PIN 1. EMITTER 2  
 2. BASE 2  
 3. COLLECTOR 1  
 4. EMITTER 1  
 5. BASE 1  
 6. COLLECTOR 2



\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**GENERIC MARKING DIAGRAM\***



XX = Specific Device Code  
 M = Month Code  
 ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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